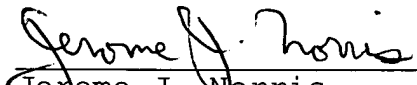


and ions of preferred energy and directionality;

c) introducing Argon and igniting the area of apparatus to generate Ar atoms and ions of preferred energy and directionality in a manner so that during ion exposure, the source-to-substrate distance is maintained such that it is less than the mean-free path or diffusion length of the Ar atoms and ions at the vacuum pressure; and

d) allowing exposure of the polycrystalline p-CdTe side of the layer to said ion beam for a period less than about 5 minutes[.] prior to forming a contact interface or semiconductor layer.

Respectfully submitted,


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